



HIGH EFFICIENCY FAST RECOVERY DIODE

MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	1 A
V_{RRM}	200 V
$t_{rr} (max)$	35 ns

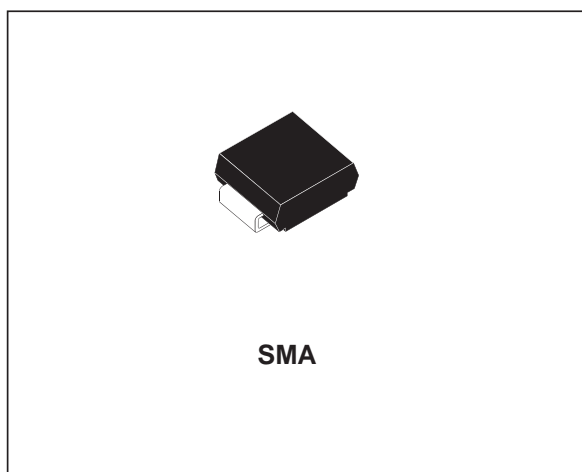
FEATURES AND BENEFITS

- VERY LOW SWITCHING LOSSES
- LOW FORWARD VOLTAGE DROP
- SURFACE MOUNT DEVICE
- FAST RECTIFIER EPITAXIAL DIODE

DESCRIPTION

Single chip rectifier suited to Switched Mode Power Supplies and high frequency DC/DC converters.

Packaged in SMA, this surface mount device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive peak reverse voltage	200	V
$I_{F(RMS)}$	RMS forward current	8	A
$I_{F(AV)}$	Average forward current	1	A
		$T_{Lead} = 125^{\circ}C$ $\delta = 0.5$	
I_{FSM}	Surge non repetitive forward current	30	A
		$t_p = 10 \text{ ms}$ Sinusoidal	
T_{stg}	Storage temperature range	- 65 to + 150	$^{\circ}C$
T_j	Maximum junction temperature	150	$^{\circ}C$

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-l)}$	Junction to lead	30	$^{\circ}C/W$

STPR120A

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Tests Conditions	Tests Conditions		Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			3	μA
		$T_j = 125^\circ\text{C}$			180	400	
V_F^{**}	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 1\text{ A}$			0.94	V
		$T_j = 150^\circ\text{C}$	$I_F = 1\text{ A}$		0.69	0.74	

Pulse test : * $t_p = 5\text{ms}$, $\delta < 2\%$
** $t_p = 380\ \mu\text{s}$, $\delta < 2\%$

RECOVERY CHARACTERISTICS

Symbol	Tests Conditions		Min.	Typ.	Max.	Unit
t_{rr}	$T_j = 25^\circ\text{C}$	$I_F = 0.50\text{ A}$ $I_R = 1\text{ A}$			25	ns
		$I_F = 1\text{ A}$ $V_R = V_{RRM}$		25	35	
t_{FR}	$T_j = 25^\circ\text{C}$	$I_F = 1\text{ A}$ Measured at 1 V			25	
V_{FP}	$T_j = 25^\circ\text{C}$	$I_F = 1\text{ A}$			5	V

To evaluate the maximum conduction losses use the following equation :
 $P = 0.62 \times I_{F(AV)} + 0.12 \times I_{F(RMS)}^2$

Fig. 1: Average forward power dissipation versus average forward current.

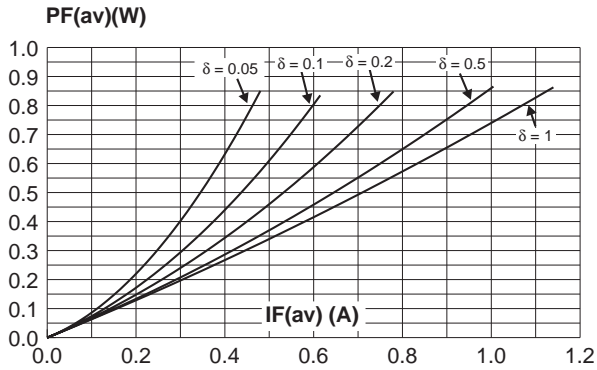


Fig. 2: Peak current versus form factor.

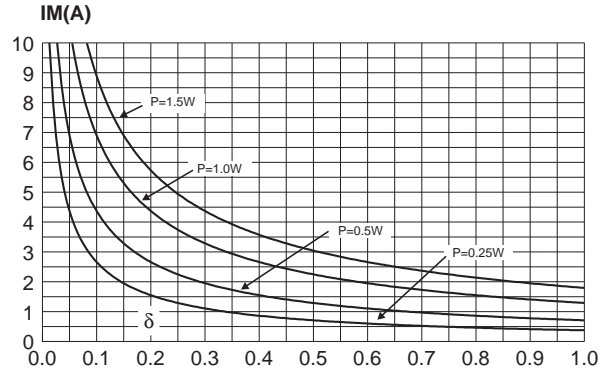


Fig. 3: Average forward current versus ambient temperature ($\delta=0.5$).

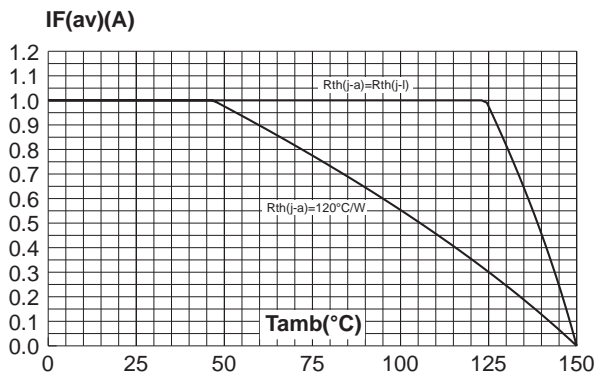


Fig. 4: Non repetitive surge peak forward current versus overload duration.

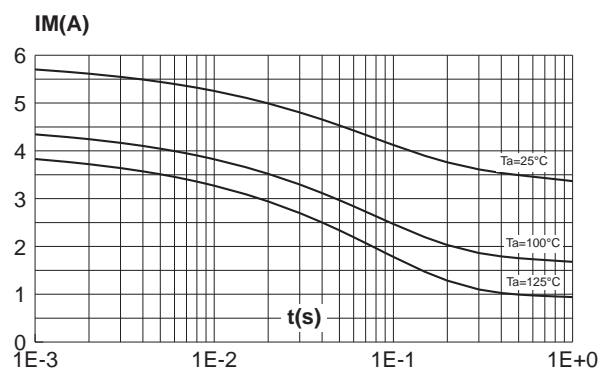


Fig. 5: Variation of thermal impedance junction to ambient versus pulse duration (Recommended pad layout, epoxy FR4, $e(Cu)=35\mu m$).

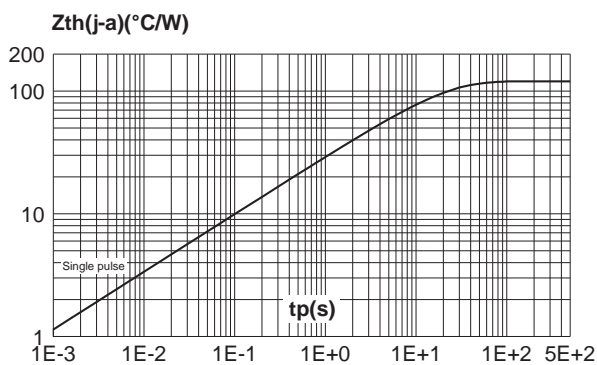


Fig. 6: Forward voltage drop versus forward current (maximum values).

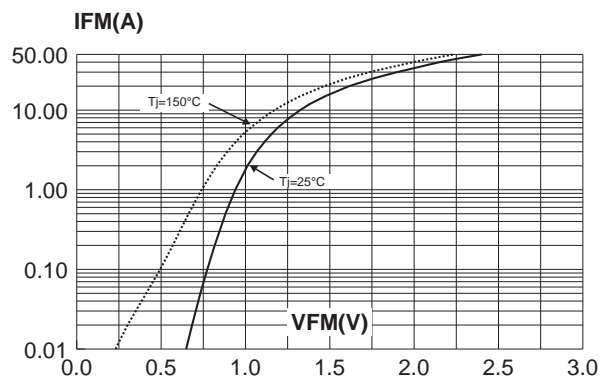


Fig. 7: Junction capacitance versus reverse voltage applied (typical values).

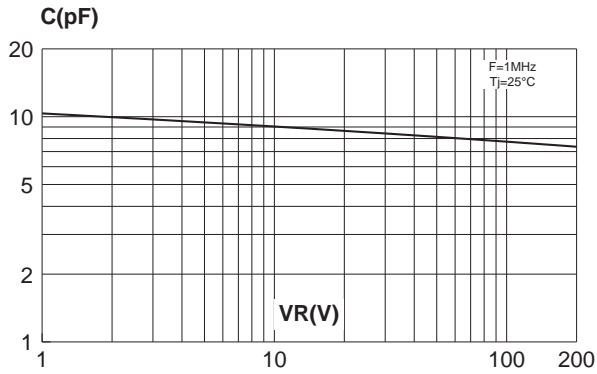


Fig. 8: Recovery charges versus dI_F/dt

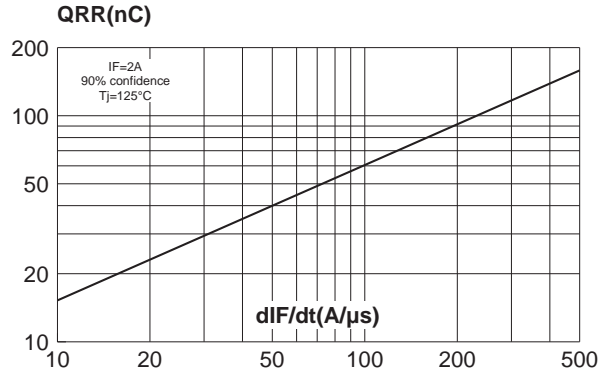


Fig. 9: Peak reverse recovery current versus dI_F/dt .

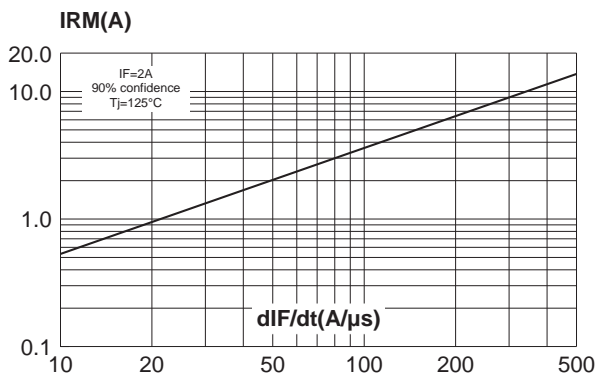
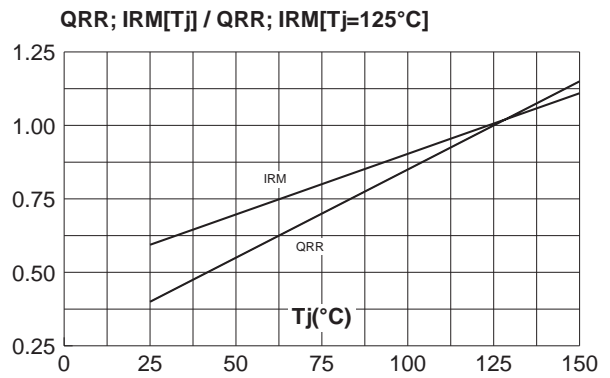
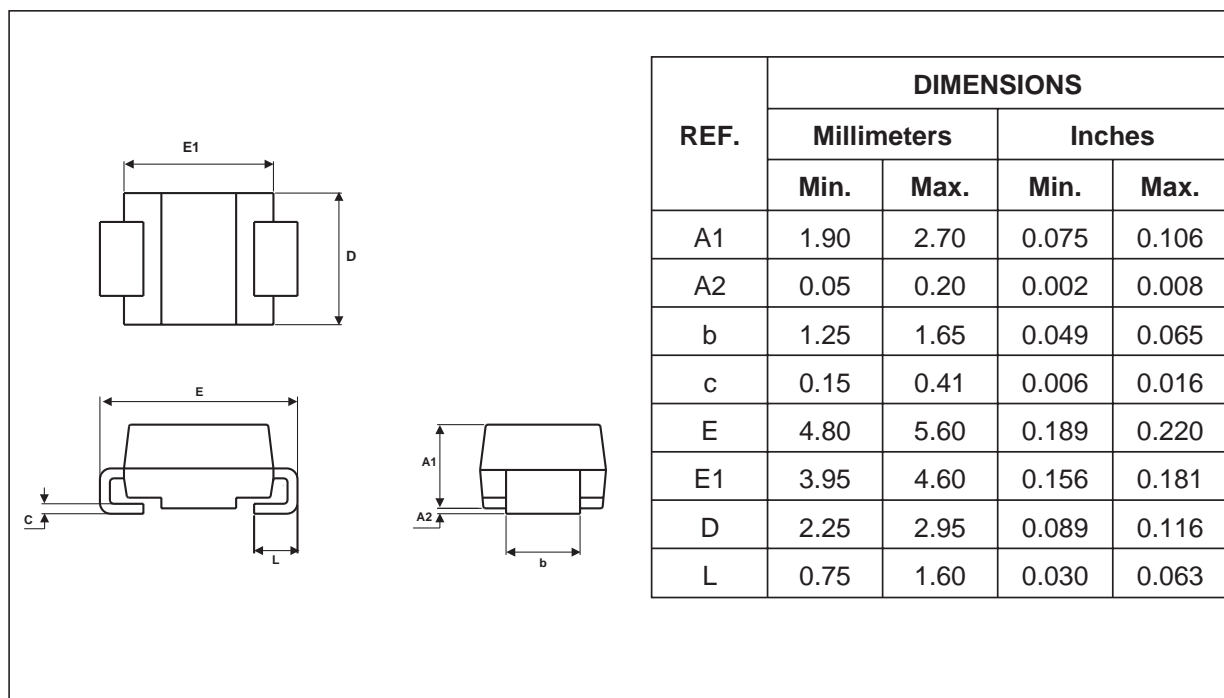


Fig. 10: Dynamic parameters versus junction temperature.

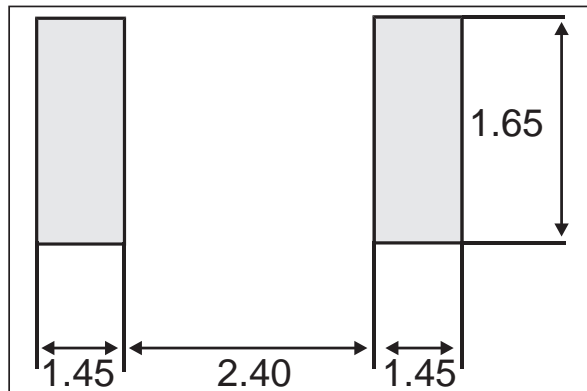


PACKAGE MECHANICAL DATA

SMA



FOOT PRINT (in millimeters)



- Marking : R12
- Cathode band is inked
- Epoxy meets UL94-V0
- Weight: 0.06g

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